

Thyristor \ Diode Module

$$V_{RRM} = 2 \times 800 \text{ V}$$

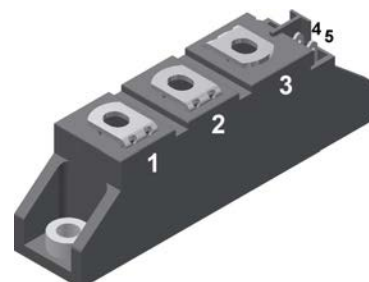
$$I_{TAV} = 60 \text{ A}$$

$$V_T = 1,24 \text{ V}$$

Phase leg

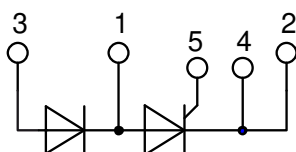
Part number

MCD56-08io1B



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

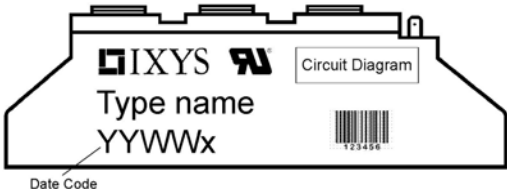
- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				900	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				800	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 800\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			200	μA
		$V_{R/D} = 800\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$			5	mA
V_T	forward voltage drop	$I_T = 100\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1,26	V
		$I_T = 200\text{ A}$				1,57	V
		$I_T = 100\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1,24	V
		$I_T = 200\text{ A}$				1,62	V
I_{TAV}	average forward current	$T_C = 85^{\circ}\text{C}$	$T_{VJ} = 125^{\circ}\text{C}$			60	A
$I_{T(RMS)}$	RMS forward current	180° sine				94	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 125^{\circ}\text{C}$			0,85	V
r_T	slope resistance					3,7	m Ω
R_{thJC}	thermal resistance junction to case					0,45	K/W
R_{thCH}	thermal resistance case to heatsink				0,2		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			222	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			1,50	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1,62	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}\text{C}$			1,28	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1,38	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			11,3	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			10,9	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}\text{C}$			8,13	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			7,87	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		74		pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 125^{\circ}\text{C}$			10	W
		$t_p = 300\text{ }\mu\text{s}$				5	W
P_{GAV}	average gate power dissipation					0,5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 150\text{ A}$				150	A/ μs
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 0,45\text{ A}/\mu\text{s};$ $I_G = 0,45\text{ A}; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 60\text{ A}$				500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$T_{VJ} = 125^{\circ}\text{C}$			1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1,5	V
			$T_{VJ} = -40^{\circ}\text{C}$			1,6	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			100	mA
			$T_{VJ} = -40^{\circ}\text{C}$			200	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}\text{C}$			0,2	V
I_{GD}	gate non-trigger current					10	mA
I_L	latching current	$t_p = 10\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			450	mA
		$I_G = 0,45\text{ A}; di_G/dt = 0,45\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$ $I_G = 0,45\text{ A}; di_G/dt = 0,45\text{ A}/\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 150\text{ A}; V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10\text{ A}/\mu\text{s}; dv/dt = 20\text{ V}/\mu\text{s}; t_p = 200\text{ }\mu\text{s}$	$T_{VJ} = 100^{\circ}\text{C}$		150		μs

Package TO-240AA				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				200	A
T _{VJ}	virtual junction temperature			-40		125	°C
T _{op}	operation temperature			-40		100	°C
T _{stg}	storage temperature			-40		125	°C
Weight					81		g
M _D	mounting torque			2,5		4	Nm
M _T	terminal torque			2,5		4	Nm
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal	13,0	9,7			mm
d _{Spb/Apb}		terminal to backside	16,0	16,0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	4800			V
		t = 1 minute		4000			V



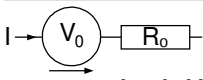
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD56-08io1B	MCD56-08io1B	Box	36	476463

Similar Part	Package	Voltage class
MCMA65PD1200TB	TO-240AA-1B	1200
MCMA85PD1200TB	TO-240AA-1B	1200

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 125^{\circ}\text{C}$



Thyristor

$V_{0\text{ max}}$

threshold voltage

0,85

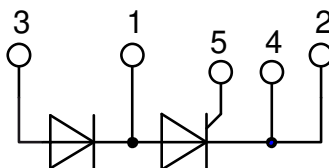
V

$R_{0\text{ max}}$

*slope resistance **

2,5

mΩ



Thyristor

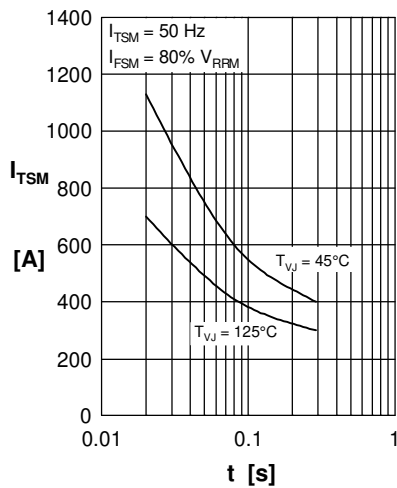


Fig. 1 Surge overload current I_{TSM} ,
 I_{FSM} : Crest value, t : duration

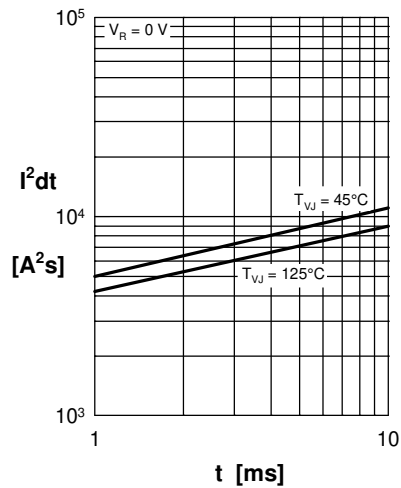


Fig. 2 I^2dt versus time (1-10 ms)

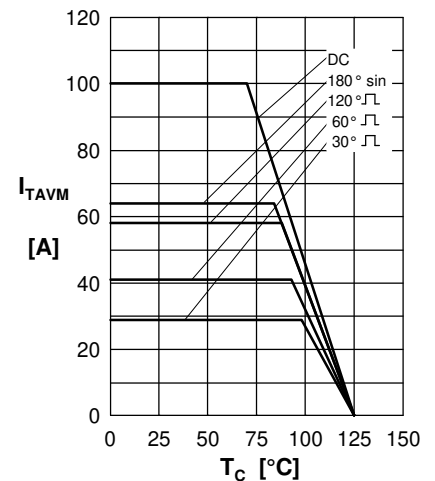


Fig. 3 Max. forward current
 at case temperature

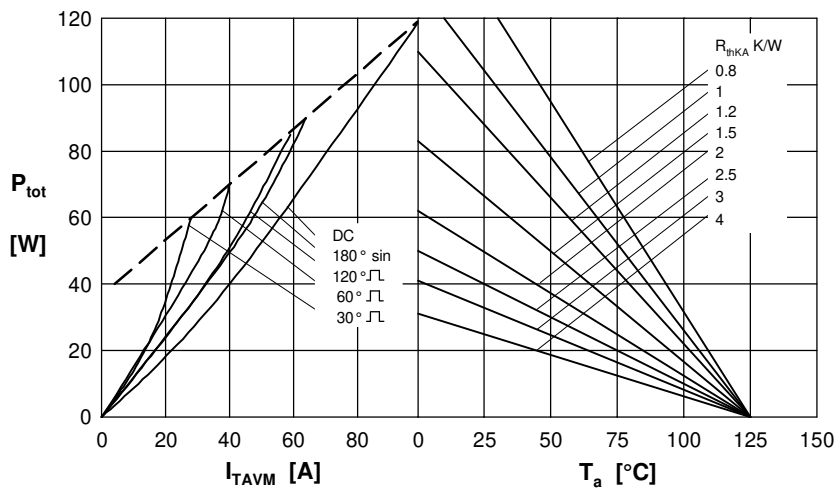


Fig. 4 Power dissipation vs. on-state current & ambient temperature
 (per thyristor or diode)

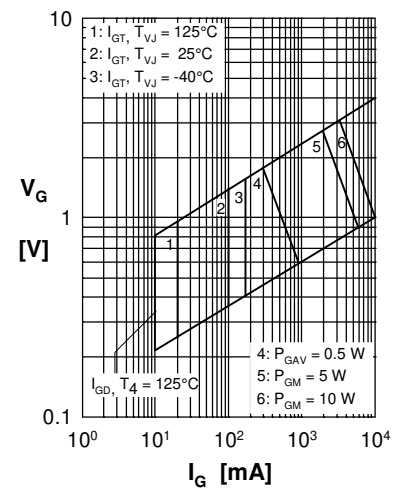


Fig. 5 Gate trigger characteristics

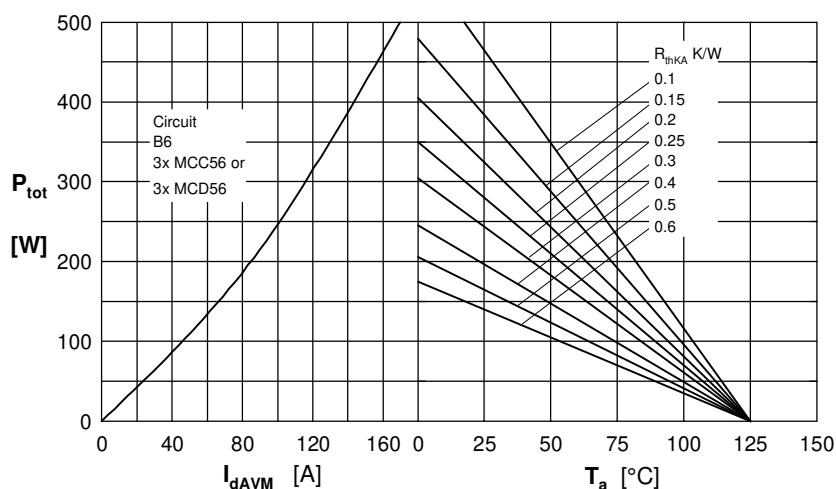


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct
 output current and ambient temperature

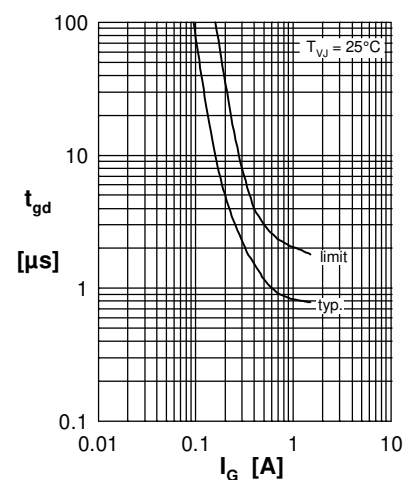


Fig. 7 Gate trigger delay time

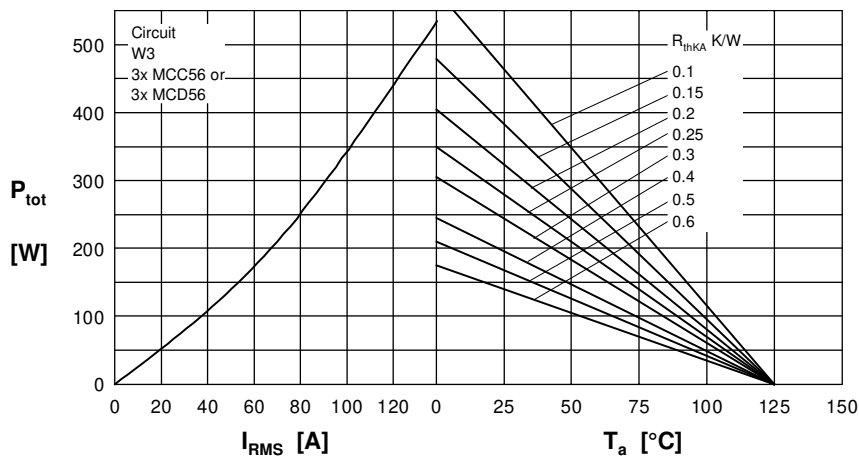
Rectifier


Fig. 8 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

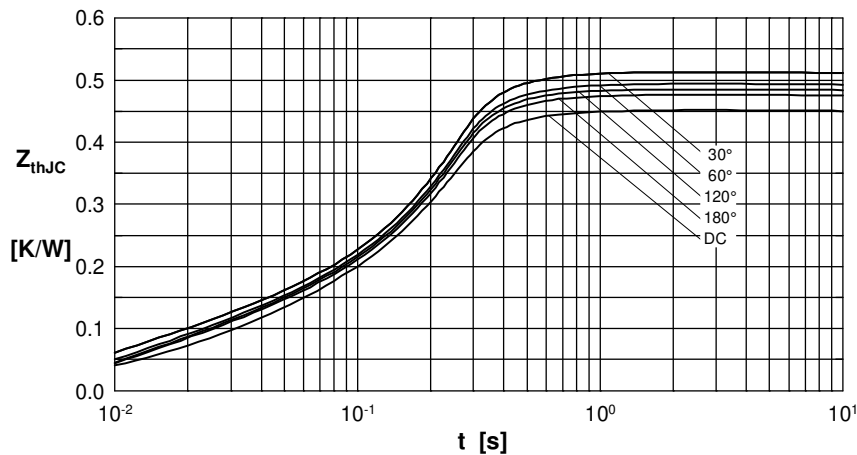


Fig. 9 Transient thermal impedance junction to case (per thyristor/diode)

R_{thJC} for various conduction angles d:

d	R_{thJC} [K/W]
DC	0.450
180°	0.470
120°	0.490
60°	0.505
30°	0.520

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.014	0.0150
2	0.026	0.0095
3	0.410	0.1750

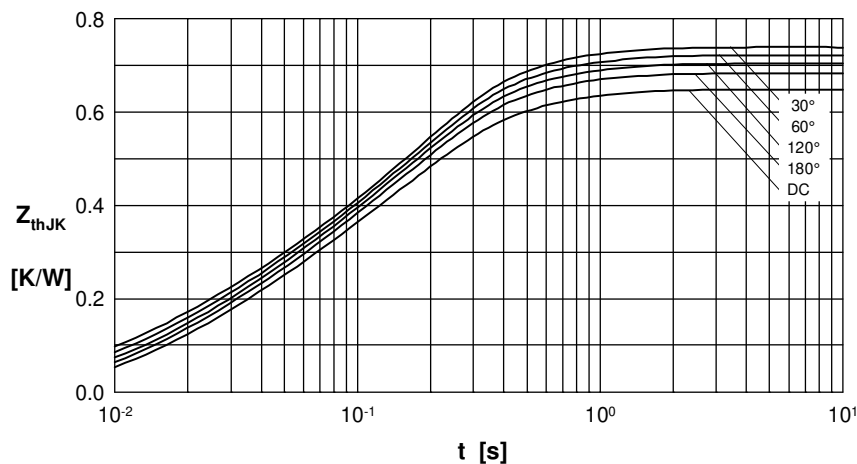


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor/diode)

R_{thJK} for various conduction angles d:

d	R_{thJK} [K/W]
DC	0.650
180°	0.670
120°	0.690
60°	0.705
30°	0.720

Constants for Z_{thJK} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.014	0.0150
2	0.026	0.0095
3	0.410	0.1750
4	0.200	0.6700